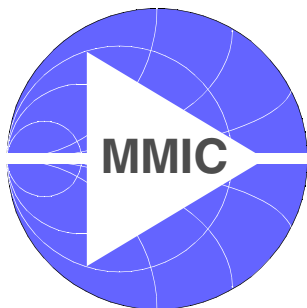


# BGA616

Silicon Germanium  
Broadband MMIC Amplifier



Wireless  
Silicon Discretes



Never stop thinking.

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**BGA616****Preliminary data sheet****Revision History:**      **2001-11-14**

Preliminary

Previous Version:      2001-07-13

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Page	Subjects (major changes since last revision)
5	Maximum ratings defined

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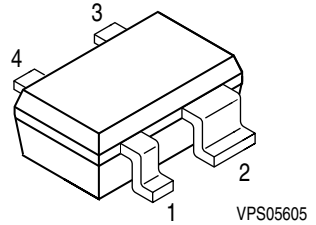
Preliminary

## Silicon Germanium Broadband MMIC Amplifier

**BGA616**

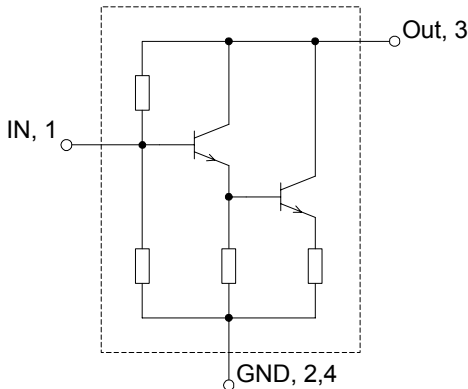
### Features

- Cascadable 50Ω-gain block
- 3 dB-bandwidth: DC to 2.7 GHz with  
18.5 dB typical gain at 1.0 GHz
- Compression point  $P_{-1dB} = 18$  dBm at 2.0 GHz
- Noise figure  $F_{50\Omega} = 2.90$  dB at 2.0 GHz
- Absolute stable
- 70 GHz  $f_T$  - Silicon Germanium technology



### Applications

- Driver amplifier for GSM/PCS/CDMA/UMTS
- Broadband amplifier for SAT-TV & LNBs
- Broadband amplifier for CATV



### Description

The BGA616 is a broadband matched, general purpose MMIC amplifier in a Darlington configuration. It is optimized for a typical supply current of 60mA.

The BGA616 is based on Infineon Technologies' B7HF Silicon Germanium technology.

**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

Type	Package	Marking	Chip
BGA616	SOT343	BPs	T0566

**Preliminary**
**Maximum Ratings**

Parameter	Symbol	Value	Unit
Device voltage	$V_D$	4.5	V
Device current	$I_D$	80	mA
Current into pin In	$I_{In}$	0.7	mA
Total power dissipation, $T_S < 78^\circ\text{C}$ <sup>1)</sup>	$P_{tot}$	360	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Ambient temperature range	$T_A$	-65 ... +150	$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-65 ... +150	$^\circ\text{C}$
Thermal resistance: junction-soldering point	$R_{thJS}$	200	K/W

Notes:

All Voltages refer to GND-Node

<sup>1)</sup>  $T_S$  is measured on the ground lead at the soldering point

**Electrical Characteristics** at  $T_A=25^\circ\text{C}$  (measured in test circuit specified in fig. 1)

 $V_{CC}=5\text{V}$ ,  $R_{Bias}=15\Omega$ , Frequency=2GHz, unless otherwise specified

Parameter	Symbol	min.	typ.	max.	Unit
Insertion power gain	$ S_{21} ^2$	-	19.5	-	dB
f = 0.1GHz		-	18.5	-	
f = 1.0GHz		-	17.5	-	
f = 2.0GHz		-		-	
Noise Figure ( $Z_S=50\Omega$ )	$F_{50\Omega}$	-	2.50	-	dB
f = 0.1GHz		-	2.80	-	
f = 1.0GHz		-	2.90	-	
f = 2.0GHz		-		-	
Output Power at 1dB Gain Compression	$P_{-1dB}$	-	18	-	dBm
Output Third Order Intercept Point	$OIP_3$	-	29	-	dBm
Input Return Loss	$RL_{In}$	-	19	-	dB
Output Return Loss	$RL_{Out}$	-	25	-	dB
Total Device Current	$I_D$	-	60	-	mA

Preliminary

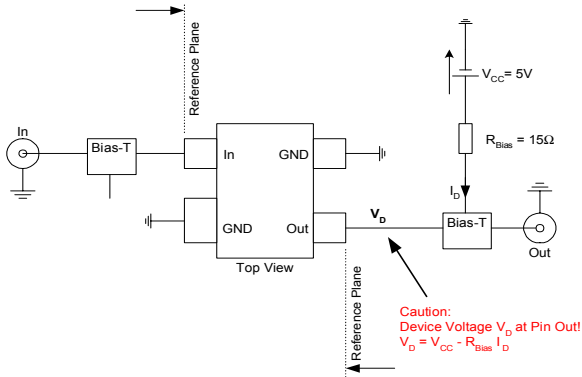


Fig.1: Test Circuit for Electrical Characteristics and S-Parameters

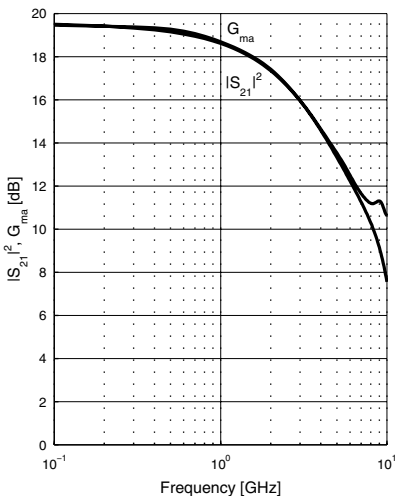
**S-Parameter**  $V_{CC}=5V$ ,  $R_{Bias}=15\Omega$  (see Electrical Characteristics for conditions)

Frequency [GHz]	S11 Mag	S11 Ang	S21 Mag	S21 Ang	S12 Mag	S12 Ang	S22 Mag	S22 Ang
0.1	0.0788	36.2	9.3218	177.9	0.0758	-0.1	0.1072	1.0
0.2	0.0822	10.5	9.3036	173.8	0.0756	1.0	0.1071	-1.2
0.4	0.0824	15.1	9.1939	166.6	0.0749	2.5	0.1082	-3.8
0.6	0.0888	17.9	9.0876	160.2	0.0748	4.4	0.1052	-7.0
0.8	0.0981	15.7	8.8024	153.5	0.0752	6.1	0.0999	-10.4
1.0	0.1033	20.0	8.5448	147.6	0.0762	8.0	0.0937	-14.0
1.2	0.1103	22.4	8.3023	141.8	0.0772	9.3	0.0860	-16.7
1.4	0.1134	20.4	8.0733	135.4	0.0782	10.6	0.0800	-20.7
1.6	0.1159	18.6	7.8136	130.5	0.0801	12.2	0.0735	-24.8
1.8	0.1113	13.6	7.5448	125.1	0.0820	13.1	0.0666	-29.8
2.0	0.1201	15.4	7.3943	120.1	0.0831	14.5	0.0578	-35.8
3.0	0.0875	7.4	6.2842	97.2	0.0969	18.2	0.0165	-116.2
4.0	0.0512	20.9	5.3567	77.5	0.1136	18.3	0.0831	164.4
5.0	0.0422	107.8	4.6655	59.3	0.1333	15.8	0.1644	147.1
6.0	0.0960	137.4	4.1016	41.5	0.1538	10.6	0.2237	129.0
7.0	0.1586	122.7	3.6045	26.0	0.1734	4.8	0.2858	116.3
8.0	0.2356	113.5	3.2953	9.3	0.1950	-3.0	0.3679	108.2

**Preliminary**

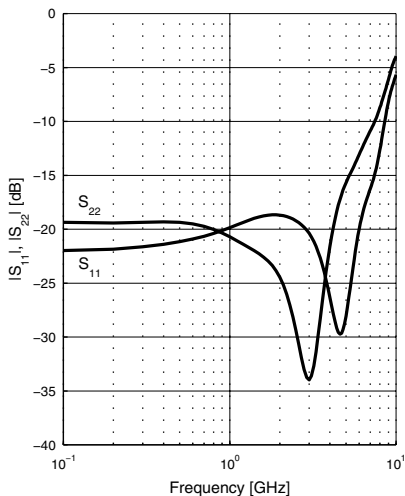
**Power Gain**  $|S_{21}|^2, G_{ma} = f(f)$

$V_{CC} = 5V, R_{Bias} = 15\Omega, I_C = 60mA$



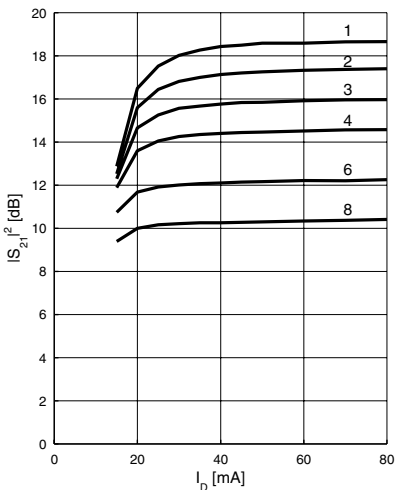
**Matching**  $|S_{11}|, |S_{22}| = f(f)$

$V_{CC} = 5V, R_{Bias} = 15\Omega, I_C = 60mA$



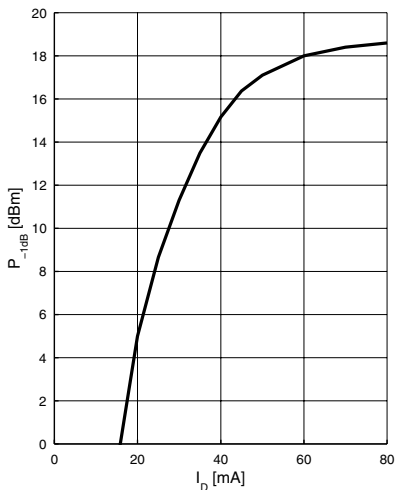
**Power Gain**  $|S_{21}| = f(I_D)$

f = parameter in GHz



**Output Compression Point**

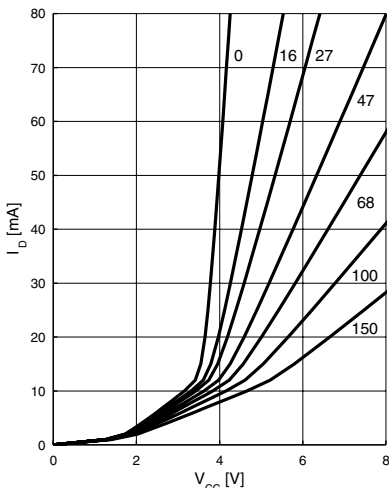
$P_{-1dB} = f(I_D), f = 2GHz$



**Preliminary**

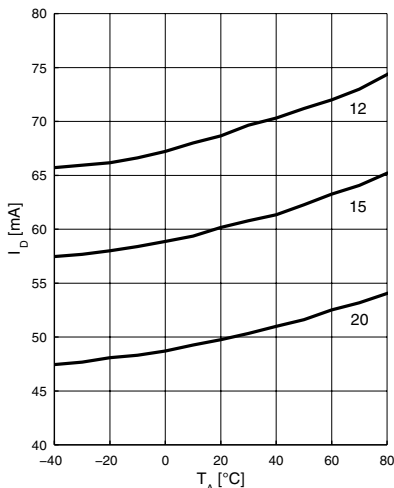
**Device Current  $I_D = f(V_{CC})$**

$R_{Bias} = \text{parameter in } \Omega$



**Device Current  $I_D = f(T_A)$**

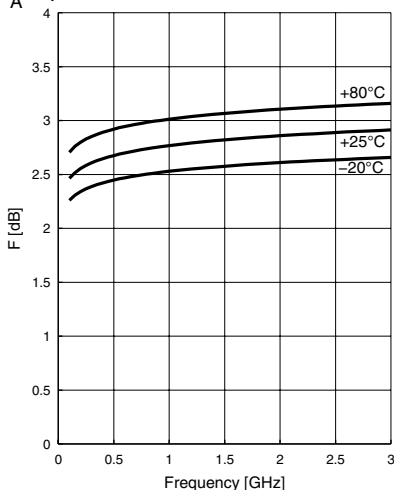
$V_D = 5V, R_{Bias} = \text{parameter in } \Omega$



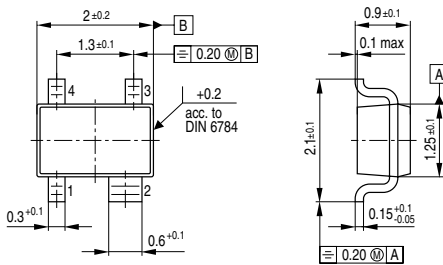
**Noise figure  $F = f(f)$**

$V_{CC} = 5V, R_{Bias} = 15\Omega, Z_S = 50\Omega$

$T_A = \text{parameter in } ^\circ C$



**Package Outline**



GPS06605